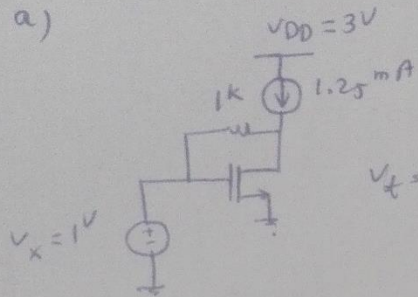


Assignment #1

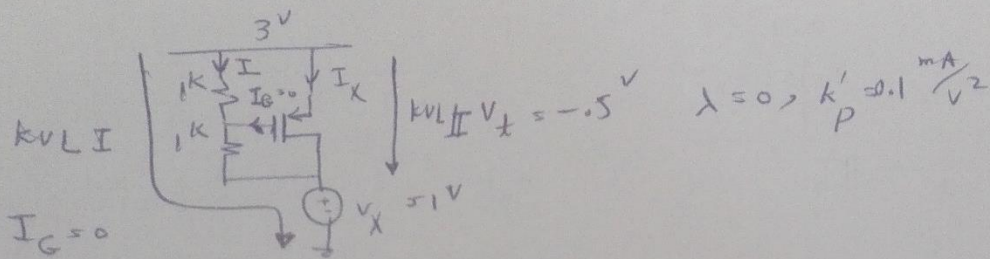
b) a)



$$V_t = 5^V \quad \lambda_n = 0 \quad \mu_{n,0} = 200 \frac{\mu A}{V^2}$$

Drain Current: I_{DQ}

1) b)



$$kV_L I: 3 = 1 \times I + 1 \times I + 1 \Rightarrow I = 1^{mA}$$

$$\Rightarrow V_{SG} = 1 \times 1 = 1V$$

Assume the trans. is in Saturation. \Rightarrow

$$I_D = I_X = \frac{1}{2} \times 0.1 \times \left(\frac{W}{L}\right) (V_{GS} - V_t)^2 \Rightarrow I_X = \frac{1}{2} \times 0.1 \times \left(\frac{5}{.5}\right) (1 - (-.5))^2 = .125^{mA}$$

Now, we should check our assumption.

The Condition for tran to be in Sati is

$$|V_{GS}| > |V_t|, |V_{DS}| > (|V_{GS}| - |V_t|)$$

$$|V_{GS}| = 1V > -.5V \checkmark$$

to find V_{DS} , $kV_L II: 3 = V_{SD} + 1 \Rightarrow V_{SD} = 2V$

$$\Rightarrow 2 > 1 - (-.5) = 1.5V \checkmark$$

So, the trans. is in Sati. \checkmark

$$I_D = 0.125^{mA}$$

$$|V_{DS}| = 2V$$

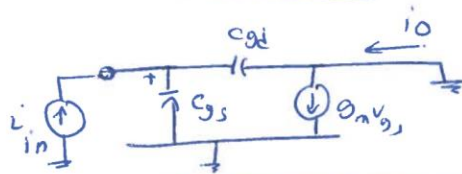
Region: Saturation

$$3) a) f_T = \frac{g_m}{2\pi(C_{gs} + C_{gd})}$$

$$\frac{i_o}{i_{in}} = \frac{g_m}{2\pi f(C_{gd} + C_{gs})}$$

$$\Rightarrow A_i \leq 1 \Rightarrow$$

$$f_T = \frac{g_m}{2\pi(C_{gd} + C_{gs})}$$



$$b) g_m = k' \left(\frac{W}{L} \right) (V_{ov})$$

$$C_{gd} = C_{ox} W$$

$$C_{gs} = \frac{2}{3} C_{ox} W (L - 2L_D) + C_{ov} W \approx \frac{2}{3} C_{ox} W L, \quad C_{gs} \gg C_{gd}$$

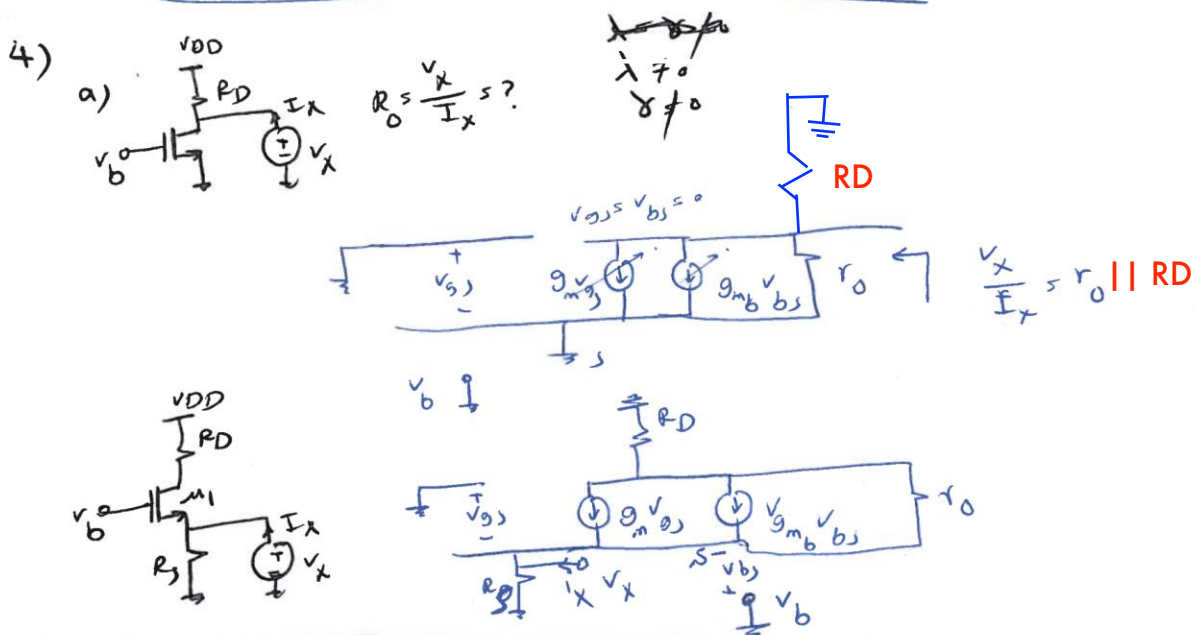
$$\Rightarrow f_T = \frac{\mu_n C_{ox} / k' \left(\frac{W}{L} \right) V_{eff}}{2\pi \frac{2}{3} C_{ox} W / L} = \frac{3 \mu_n V_{eff}}{4\pi L^2}$$

$$c) I_D = I_0 e^{\frac{V_{gs}}{nV_T}} \Rightarrow g_m = \frac{\partial I_D}{\partial V_{gs}} = \frac{I_D}{nV_T}$$

$$\Rightarrow f_T = \frac{g_m}{2\pi(C_{gs} + C_{gd})} = \frac{I_D}{2\pi nV_T(C_{gs} + C_{gd})}$$

$$C_{gs} = C_{gd} = C_{ox} \frac{W}{L} \Rightarrow f_T = \frac{I_D}{4\pi nV_T C_{ox} \frac{W}{L}}$$

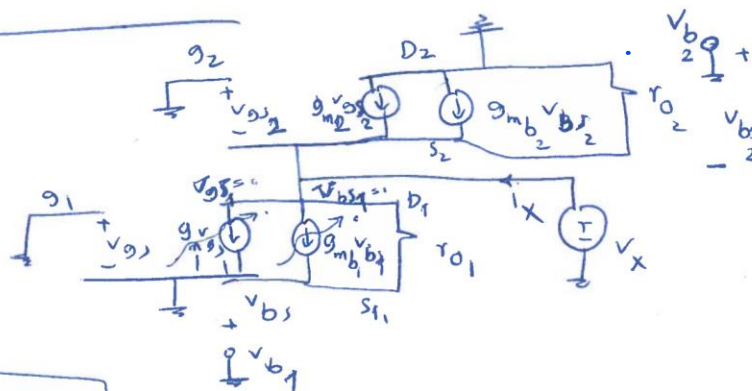
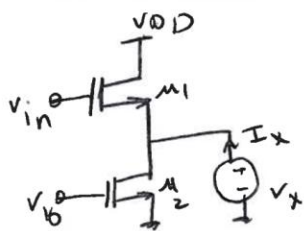
d) Although the denominator of f_T in part c is smaller than that of Part (a), its I_D is also (much) smaller than I_D in part a. So, f_T of trans. in sub-threshold is comparable or smaller than f_T in strong inversion.



$$R_{out} = \frac{v_x}{I_x} = \left[\frac{RD}{1 + (g_m + g_{mb})r_o} + \frac{1}{g_m + g_{mb}} || r_o || RS \right]$$

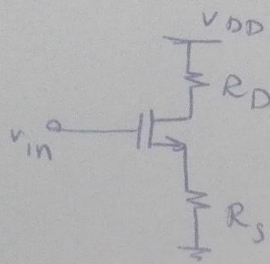
$$R_{out} = R_s \parallel \left\{ \frac{R_D}{1 + (g_{mb} + g_m)r_o} + \left(r_o \parallel \frac{1}{g_{mb} + g_m} \right) \right\} =$$

$$R_s \parallel \left\{ \frac{R_D + r_o}{1 + (g_{mb} + g_m)r_o} \right\}$$



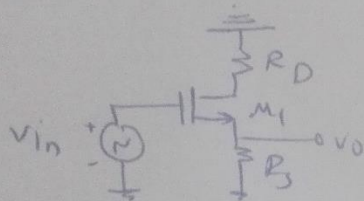
$$\frac{v_x}{i_x} = r_{o1} \parallel r_{o2} \parallel \frac{1}{g_m + g_{mb2}}$$

5) a) Finding the small signal gain:

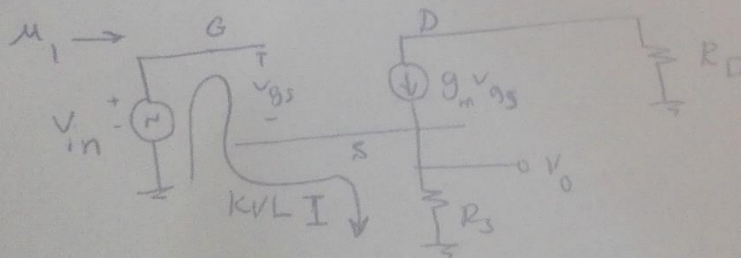


$$\lambda = \gamma = 0$$

To find gain, First all DC independent sources are required to be set to ZERO \Rightarrow



Using small signal model for the transistor:

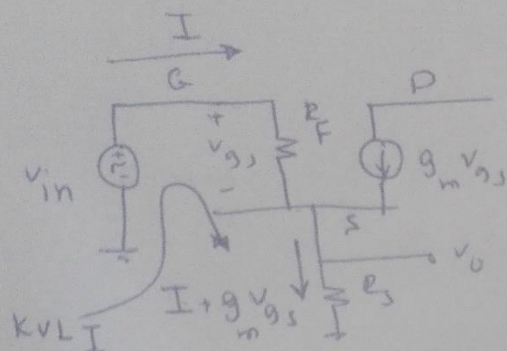
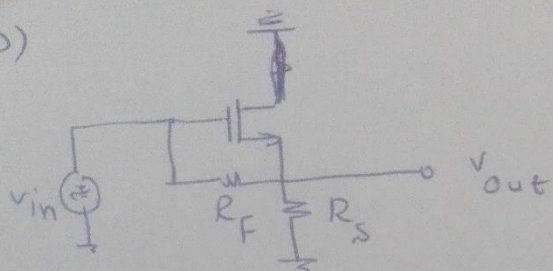


$$\text{KVL I: } v_{in} = v_{gs} + R_S g_m v_{gs} \Rightarrow v_{gs} = \frac{v_{in}}{1 + g_m R_S}$$

$$\text{and } v_o = R_S \times g_m v_{gs} \Rightarrow v_o = g_m R_S \times \frac{1}{1 + g_m R_S}$$

$$\Rightarrow A_v = \frac{v_o}{v_{in}} = \frac{g_m R_S}{1 + g_m R_S}$$

5) b)



$$\text{KVL I: } v_{in} = R_F I + R_S (g_m v_{gs} + I) \quad \text{(I)}$$

and

$$v_{gs} = R_F I \quad \text{(II)}$$

$$\text{(II)} \rightarrow \text{(I)} \Rightarrow v_{in} = R_F I + R_S I + g_m R_S (R_F I)$$

$$\Rightarrow I = \frac{v_{in}}{R_F + R_S + R_F R_S g_m}$$

$$v_o = R_S (I + g_m v_{gs}) = \frac{R_S v_{in}}{R_F + R_S + R_F R_S g_m} + \frac{g_m R_S R_F v_{in}}{R_F + R_S + R_F R_S g_m}$$

$$\Rightarrow A_v = \frac{R_S + g_m R_S R_F}{R_F + R_S + R_F R_S g_m}$$